# **Dual Schottky Barrier Diodes**

Application circuit designs are moving toward the consolidation of device count and into smaller packages. The new SOT-363 package is a solution which simplifies circuit design, reduces device count, and reduces board space by putting two discrete devices in one small six-leaded package. The SOT-363 is ideal for low-power surface mount applications where board space is at a premium, such as portable products.

### **Surface Mount Comparisons:**

	SOT-363	SOT-23
Area (mm²)	4.6	7.6
Max Package P <sub>D</sub> (mW)	120	225
Device Count	2	1

### **Space Savings:**

Package	1 x SOT-23	2 x SOT-23
SOT-363	40%	70%

The MBD110DW and MBD330DW devices are spin-offs of our popular MMBD101LT1 and MMBD301LT1 SOT-23 devices. They are designed for high-efficiency UHF and VHF detector applications. Readily available to many other fast switching RF and digital applications.

# **Features**

- Extremely Low Minority Carrier Lifetime
- Very Low Capacitance
- Low Reverse Leakage
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

### **MAXIMUM RATINGS**

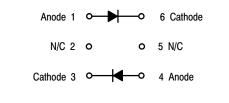
Ratin	Symbol	Value	Unit	
Reverse Voltage	MBD110DWT1G MBD330DWT1G	V <sub>R</sub>	7.0 30	V
Forward Current (DC)	MBD330DWT1G	IF	200 Max	mA
Forward Power Dissipa	P <sub>F</sub>	120	mW	
Junction Temperature	TJ	-55 to +125	°C	
Storage Temperature R	T <sub>stg</sub>	-55 to +150	°C	

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



# ON Semiconductor®

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SC-88 / SOT-363 CASE 419B STYLE 6

#### **MARKING DIAGRAM**



xx = Device Code

Refer to Ordering Table,

page 2

M = Date Code

= Pb-Free Package

(Note: Microdot may be in either location)

#### **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

1

# **ELECTRICAL CHARACTERISTICS** ( $T_A = 25^{\circ}C$ unless otherwise noted)

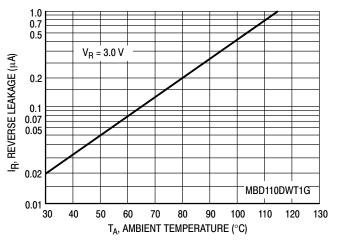
Characteristic		Symbol	Min	Тур	Max	Unit
Reverse Breakdown Voltage (I <sub>R</sub> = 10 μA)	MBD110DWT1G MBD330DWT1G	V <sub>(BR)R</sub>	7.0 30	10 -	- -	V
Diode Capacitance (V <sub>R</sub> = 0, f = 1.0 MHz, Note 1)	MBD110DWT1G	C <sub>D</sub>	-	0.88	1.0	pF
Total Capacitance (V <sub>R</sub> = 15 Volts, f = 1.0 MHz)	MBD330DWT1G	C <sub>T</sub>	-	0.9	1.5	pF
Reverse Leakage (V <sub>R</sub> = 3.0 V) (V <sub>R</sub> = 25 V)	MBD110DWT1G MBD330DWT1G	I <sub>R</sub>	- -	0.02 13	0.25 200	μA nA
Noise Figure (f = 1.0 GHz, Note 2)	MBD110DWT1G	NF	-	6.0	_	dB
Forward Voltage ( $I_F = 10 \text{ mA}$ ) ( $I_F = 1.0 \text{ mA}$ ) ( $I_F = 1.0 \text{ mA}$ ) ( $I_F = 1.0 \text{ mA}$ )	MBD110DWT1G MBD330DWT1G	V <sub>F</sub>	- - -	0.5 0.38 0.52	0.6 0.45 0.6	V

# **ORDERING INFORMATION**

Device	Marking	Package	Shipping <sup>†</sup>
MBD110DWT1G	M4	SC-88 / SOT-363	3000 Units / Tape & Reel
MBD330DWT1G	T4	(Pb-Free)	oooo oniio / Tape a rieei

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# TYPICAL CHARACTERISTICS MBD110DWT1G



1.0 T<sub>A</sub> = 85°C

T<sub>A</sub> = -40°C

MBD110DWT1G

0.1

0.3

0.4

0.5

0.6

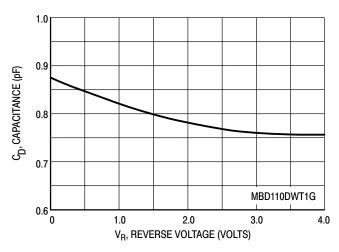
0.7

0.8

V<sub>F</sub>, FORWARD VOLTAGE (VOLTS)

Figure 1. Reverse Leakage

Figure 2. Forward Voltage



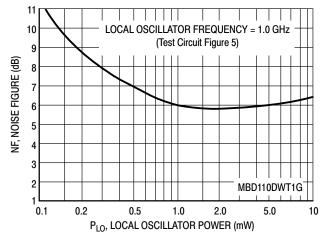


Figure 3. Capacitance

Figure 4. Noise Figure

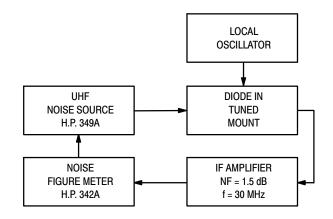
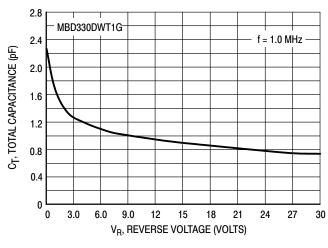


Figure 5. Noise Figure Test Circuit

# NOTES ON TESTING AND SPECIFICATIONS

- Note 1 C<sub>D</sub> and C<sub>T</sub> are measured using a capacitance bridge (Boonton Electronics Model 75A or equivalent)
- Note 2 Noise figure measured with diode under test in tuned diode mount using UHF noise source and local oscillator (LO) frequency of 1.0 GHz. The LO power is adjusted for 1.0 mW. IF amplifier NF = 1.5 dB, f = 30 MHz, see Figure 5.
- Note  $3 L_S$  is measured on a package having a short instead of a die, using an impedance bridge (Boonton Radio Model 250A RX Meter).

# TYPICAL CHARACTERISTICS MBD330DWT1G



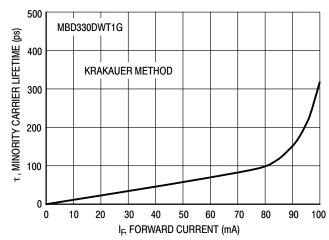
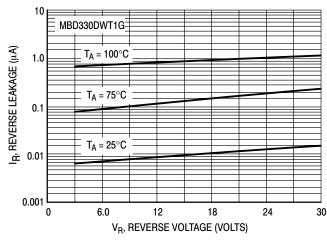


Figure 6. Total Capacitance

Figure 7. Minority Carrier Lifetime



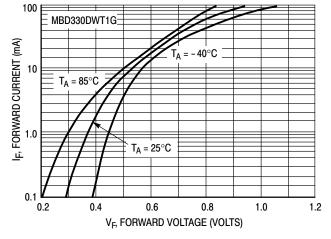
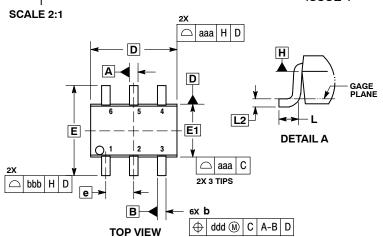


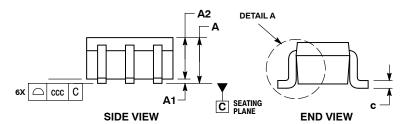
Figure 8. Reverse Leakage

Figure 9. Forward Voltage

### SC-88/SC70-6/SOT-363 CASE 419B-02 **ISSUE Y**

**DATE 11 DEC 2012** 





#### NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
   CONTROLLING DIMENSION: MILLIMETERS
- CONTROLLING DIMENSION: MILLIMETERS.
  DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH,
- DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.20 PER END. DIMENSIONS D AND E1 AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY AND DATUM H. DATUMS A AND B ARE DETERMINED AT DATUM H. DIMENSIONS b AND c APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN 0.08 AND 0.15 FROM THE TIP.

- DIMENSION & DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 TOTAL IN EXCESS OF DIMENSION 6 AT MAXIMUM MATERIAL CONDITION. THE DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OF THE FOOT.

	MIL	LIMETE	RS	INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α			1.10			0.043
A1	0.00		0.10	0.000		0.004
A2	0.70	0.90	1.00	0.027	0.035	0.039
b	0.15	0.20	0.25	0.006	0.008	0.010
С	0.08	0.15	0.22	0.003	0.006	0.009
D	1.80	2.00	2.20	0.070	0.078	0.086
E	2.00	2.10	2.20	0.078	0.082	0.086
E1	1.15	1.25	1.35	0.045	0.049	0.053
е		0.65 BSC			.026 BS	С
L	0.26	0.36	0.46	0.010	0.014	0.018
L2		0.15 BS	C	0.006 BSC		
aaa		0.15		0.006		
bbb	0.30			0.012		
ccc	0.10 0.004					
ddd		0.10		0.004		

### **GENERIC MARKING DIAGRAM\***



XXX = Specific Device Code

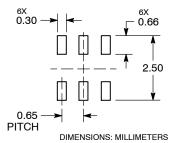
= Date Code\*

= Pb-Free Package (Note: Microdot may be in either location)

\*Date Code orientation and/or position may vary depending upon manufacturing location.

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

# **RECOMMENDED SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

## **STYLES ON PAGE 2**

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## SC-88/SC70-6/SOT-363 CASE 419B-02 ISSUE Y

**DATE 11 DEC 2012** 

STYLE 1: PIN 1. EMITTER 2 2. BASE 2 3. COLLECTOR 1 4. EMITTER 1 5. BASE 1 6. COLLECTOR 2	STYLE 2: CANCELLED	STYLE 3: CANCELLED	STYLE 4: PIN 1. CATHODE 2. CATHODE 3. COLLECTOR 4. EMITTER 5. BASE 6. ANODE	STYLE 5: PIN 1. ANODE 2. ANODE 3. COLLECTOR 4. EMITTER 5. BASE 6. CATHODE	STYLE 6: PIN 1. ANODE 2 2. N/C 3. CATHODE 1 4. ANODE 1 5. N/C 6. CATHODE 2
STYLE 7: PIN 1. SOURCE 2 2. DRAIN 2 3. GATE 1 4. SOURCE 1 5. DRAIN 1 6. GATE 2	STYLE 8: CANCELLED	STYLE 9: PIN 1. EMITTER 2 2. EMITTER 1 3. COLLECTOR 1 4. BASE 1 5. BASE 2 6. COLLECTOR 2	STYLE 10: PIN 1. SOURCE 2 2. SOURCE 1 3. GATE 1 4. DRAIN 1 5. DRAIN 2 6. GATE 2	STYLE 11: PIN 1. CATHODE 2 2. CATHODE 2 3. ANODE 1 4. CATHODE 1 5. CATHODE 1 6. ANODE 2	STYLE 12: PIN 1. ANODE 2 2. ANODE 2 3. CATHODE 1 4. ANODE 1 5. ANODE 1 6. CATHODE 2
STYLE 13: PIN 1. ANODE 2. N/C 3. COLLECTOR 4. EMITTER 5. BASE 6. CATHODE	STYLE 14: PIN 1. VREF 2. GND 3. GND 4. IOUT 5. VEN 6. VCC	STYLE 15: PIN 1. ANODE 1 2. ANODE 2 3. ANODE 3 4. CATHODE 3 5. CATHODE 2 6. CATHODE 1	STYLE 16: PIN 1. BASE 1 2. EMITTER 2 3. COLLECTOR 2 4. BASE 2 5. EMITTER 1 6. COLLECTOR 1	STYLE 17: PIN 1. BASE 1 2. EMITTER 1 3. COLLECTOR 2 4. BASE 2 5. EMITTER 2 6. COLLECTOR 1	STYLE 18: PIN 1. VIN1 2. VCC 3. VOUT2 4. VIN2 5. GND 6. VOUT1
STYLE 19: PIN 1. I OUT 2. GND 3. GND 4. V CC 5. V EN 6. V REF	STYLE 20: PIN 1. COLLECTOR 2. COLLECTOR 3. BASE 4. EMITTER 5. COLLECTOR 6. COLLECTOR	STYLE 21: PIN 1. ANODE 1 2. N/C 3. ANODE 2 4. CATHODE 2 5. N/C 6. CATHODE 1	STYLE 22: PIN 1. D1 (i) 2. GND 3. D2 (i) 4. D2 (c) 5. VBUS 6. D1 (c)	STYLE 23: PIN 1. Vn 2. CH1 3. Vp 4. N/C 5. CH2 6. N/C	STYLE 24: PIN 1. CATHODE 2. ANODE 3. CATHODE 4. CATHODE 5. CATHODE 6. CATHODE
STYLE 25: PIN 1. BASE 1 2. CATHODE 3. COLLECTOR 2 4. BASE 2 5. EMITTER 6. COLLECTOR 1	STYLE 26: PIN 1. SOURCE 1 2. GATE 1 3. DRAIN 2 4. SOURCE 2 5. GATE 2 6. DRAIN 1	STYLE 27: PIN 1. BASE 2 2. BASE 1 3. COLLECTOR 1 4. EMITTER 1 5. EMITTER 2 6. COLLECTOR 2	STYLE 28: PIN 1. DRAIN 2. DRAIN 3. GATE 4. SOURCE 5. DRAIN 6. DRAIN	STYLE 29: PIN 1. ANODE 2. ANODE 3. COLLECTOR 4. EMITTER 5. BASE/ANODE 6. CATHODE	STYLE 30: PIN 1. SOURCE 1 2. DRAIN 2 3. DRAIN 2 4. SOURCE 2 5. GATE 1 6. DRAIN 1

Note: Please refer to datasheet for style callout. If style type is not called out in the datasheet refer to the device datasheet pinout or pin assignment.

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